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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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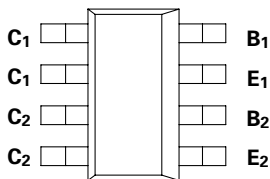
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



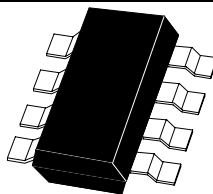
SM-8 DUAL NPN MEDIUM POWER HIGH GAIN TRANSISTORS

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ZDT1049



PARTMARKING DETAIL – T1049



SM-8
(8 LEAD SOT223)

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	20	A
Continuous Collector Current	I_C	5	A
Base Current	I_B	500	mA
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^\circ\text{C}^*$ Any single die "on" Both die "on" equally	P_{tot}	2.25 2.75	W W
Derate above 25°C^* Any single die "on" Both die "on" equally		18 22	mW/°C mW/°C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/W °C/W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	120		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CES}	80	120		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CEO}	25	35		V	$I_C=10\text{mA}$
Collector-Emitter Breakdown Voltage	V_{CEV}	80	120		V	$I_C=100\mu\text{A}, V_{EB}=1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.75		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		0.3	10	nA	$V_{CB}=50\text{V}$
Emitter Cut-Off Current	I_{EBO}		0.3	10	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}		0.3	10	nA	$V_{CES}=50\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		30 60 125 155	45 80 180 220	mV mV mV mV	$I_C=0.5\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=2\text{A}, I_B=10\text{mA}^*$ $I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		890	950	mV	$I_C=4\text{A}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		820	900	mV	$I_C=4\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	250 300 300 200 35	430 450 450 350 70	1200		$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=4\text{A}, V_{CE}=2\text{V}^*$ $I_C=20\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T		180		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=50\text{MHz}$
Output Capacitance	C_{obo}		45	60	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn - On Time	t_{on}		125		ns	$I_C=4\text{A}, I_B=40\text{mA}, V_{CC}=10\text{V}$
Turn -Off Time	t_{off}		380		ns	$I_C=4\text{A}, I_B=\pm 40\text{mA}, V_{CC}=10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

